

Photoluminescence-imaging-based Evaluation of Non-uniform CdTe Degradation

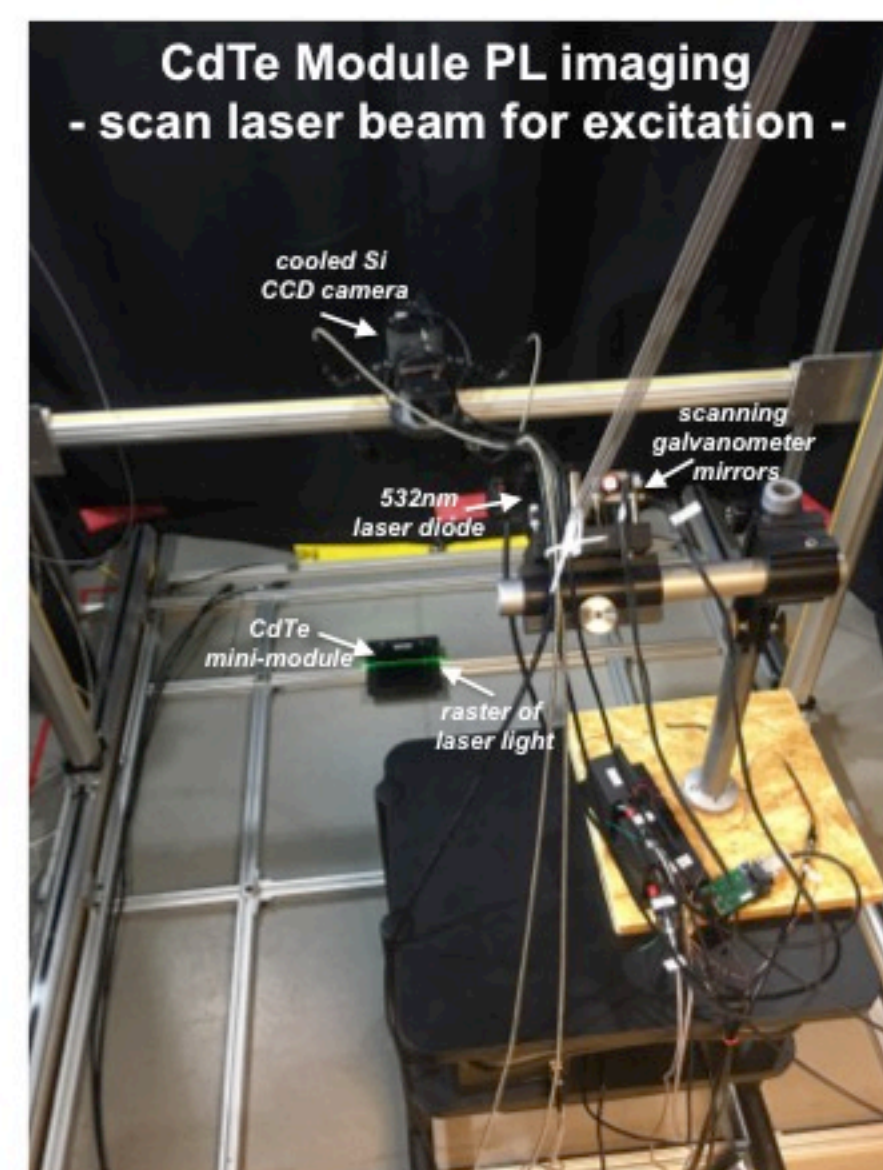
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Study module degradation mechanisms by understanding the semiconductor device at the microscopic level, such as kinetics of impurities, changes in materials, and damage to device architecture.

CdTe mini-module
(cells are ~5 mm wide)



Princeton Instruments
PIXIS 1024BR

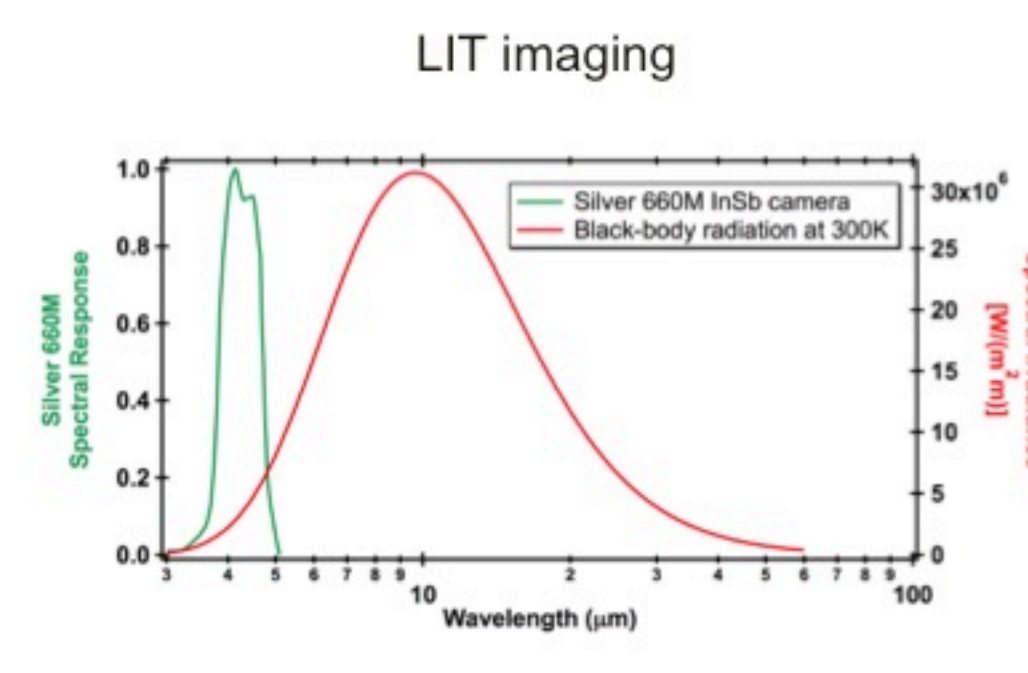
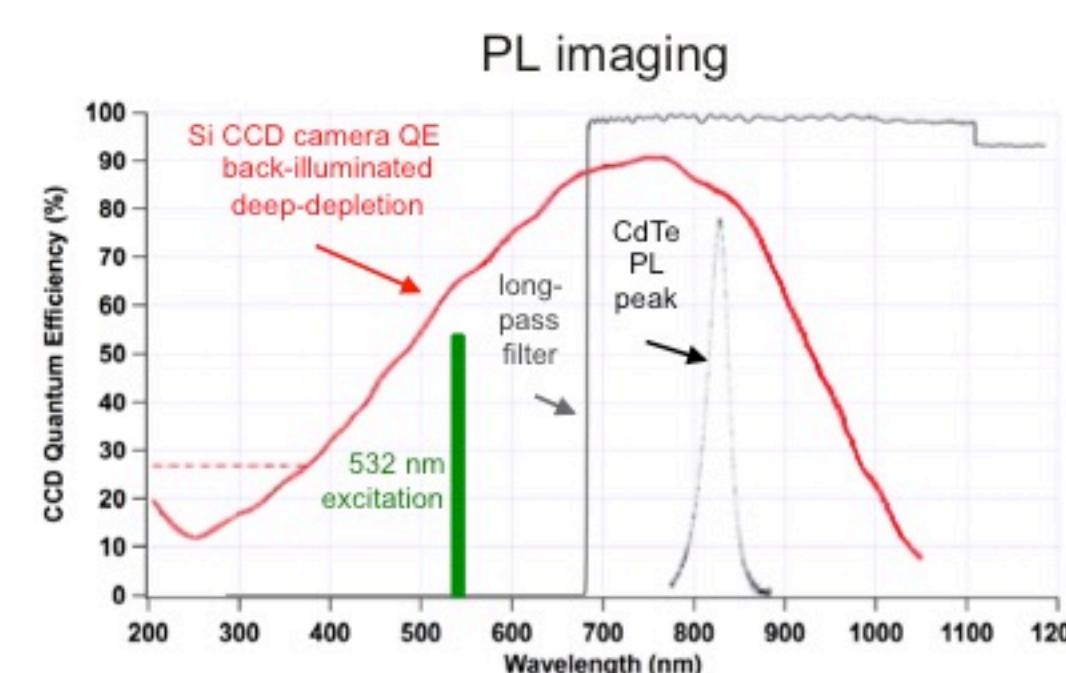


- Photoluminescence (PL) imaging
- Electroluminescence (EL) imaging

Imaging for photovoltaics

The cameras used for the various techniques are listed below:

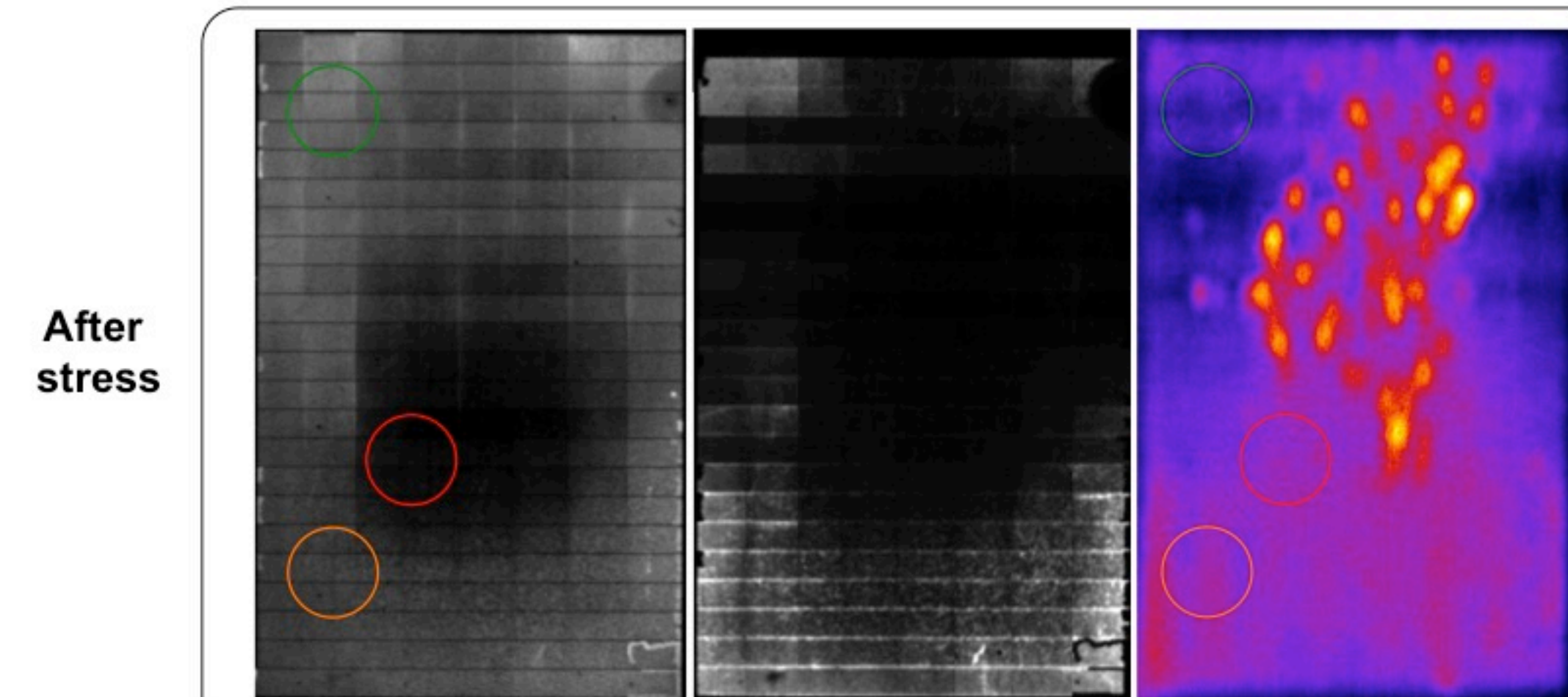
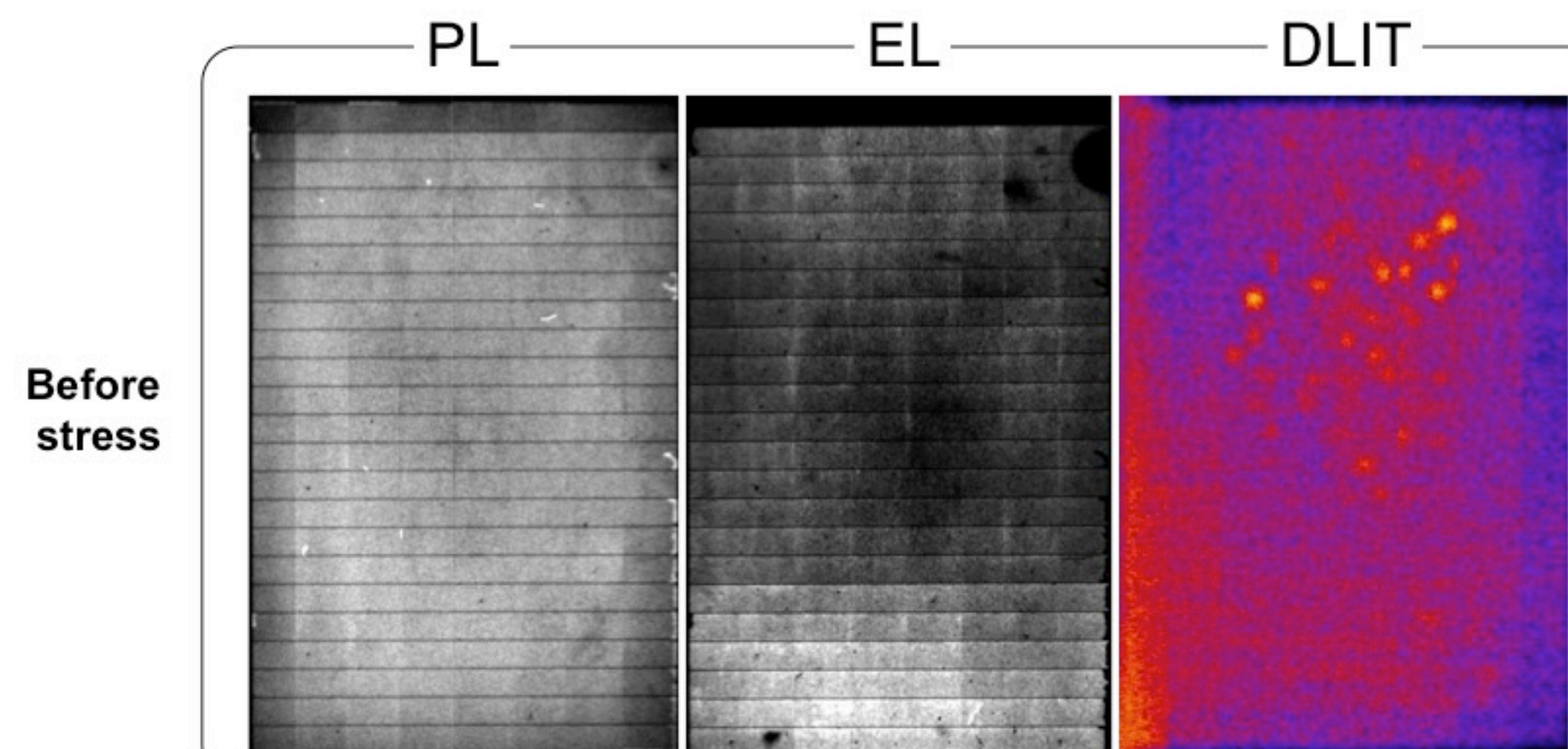
- Silicon charge-coupled device (CCD) 16-bit camera with 1024 x 1024 pixels (13μm pixel pitch), cooled to ~-60°C
- InSb 14-bit lock-in camera with 640 x 512 pixels (15μm pixel pitch), cooled to ~-80K



Cedip Silver 660M
FLIR SC5600-M

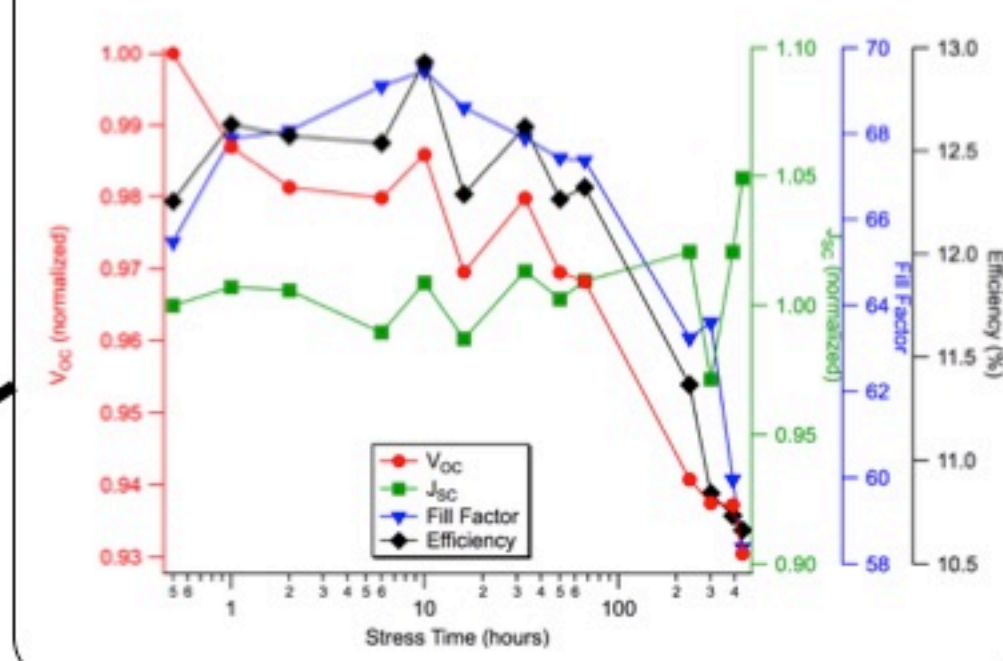
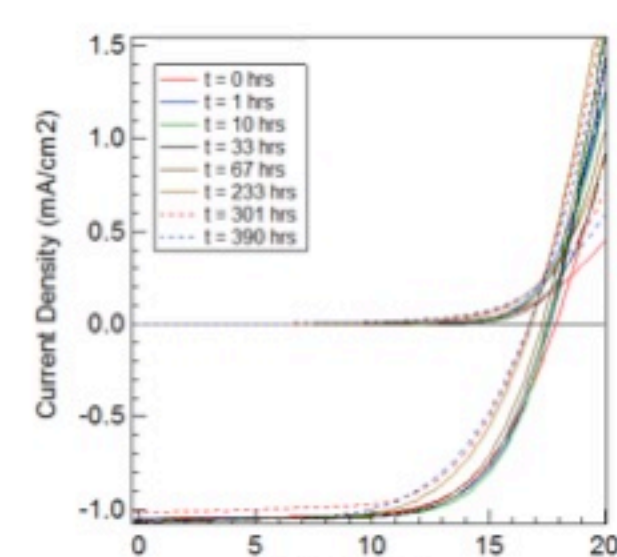


- Lock-In Thermography
 - ❖ Dark (DLIT)
 - Forward bias
 - Reverse bias
 - ❖ Illuminated (ILIT)



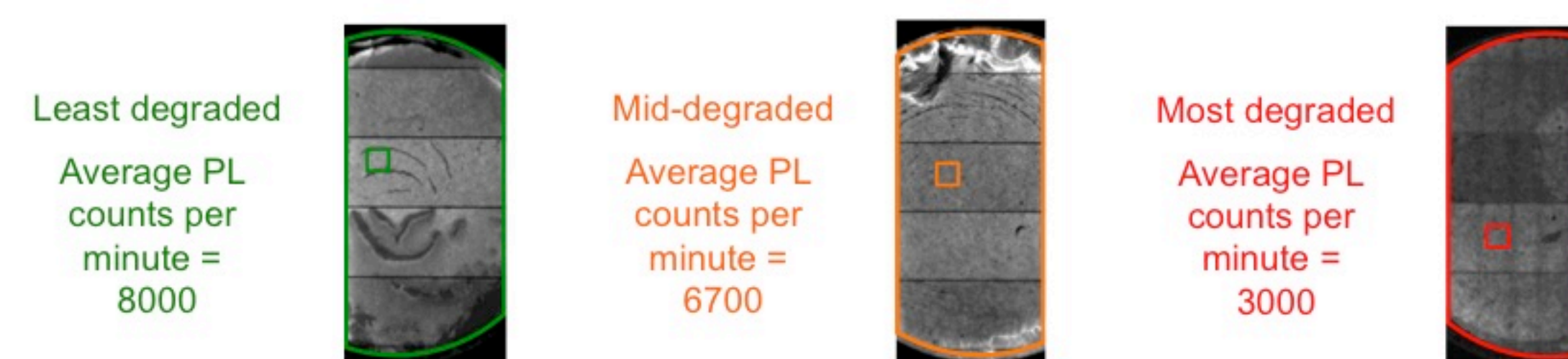
- PL – raster pattern, 532 nm laser diode, ~1 mm spot size, ~1-Sun intensity excitation.
- EL ~1/3 J_{SC} current excitation.
- DLIT – forward bias, ~1/3 J_{SC} current excitation.

Stress (light/heat)

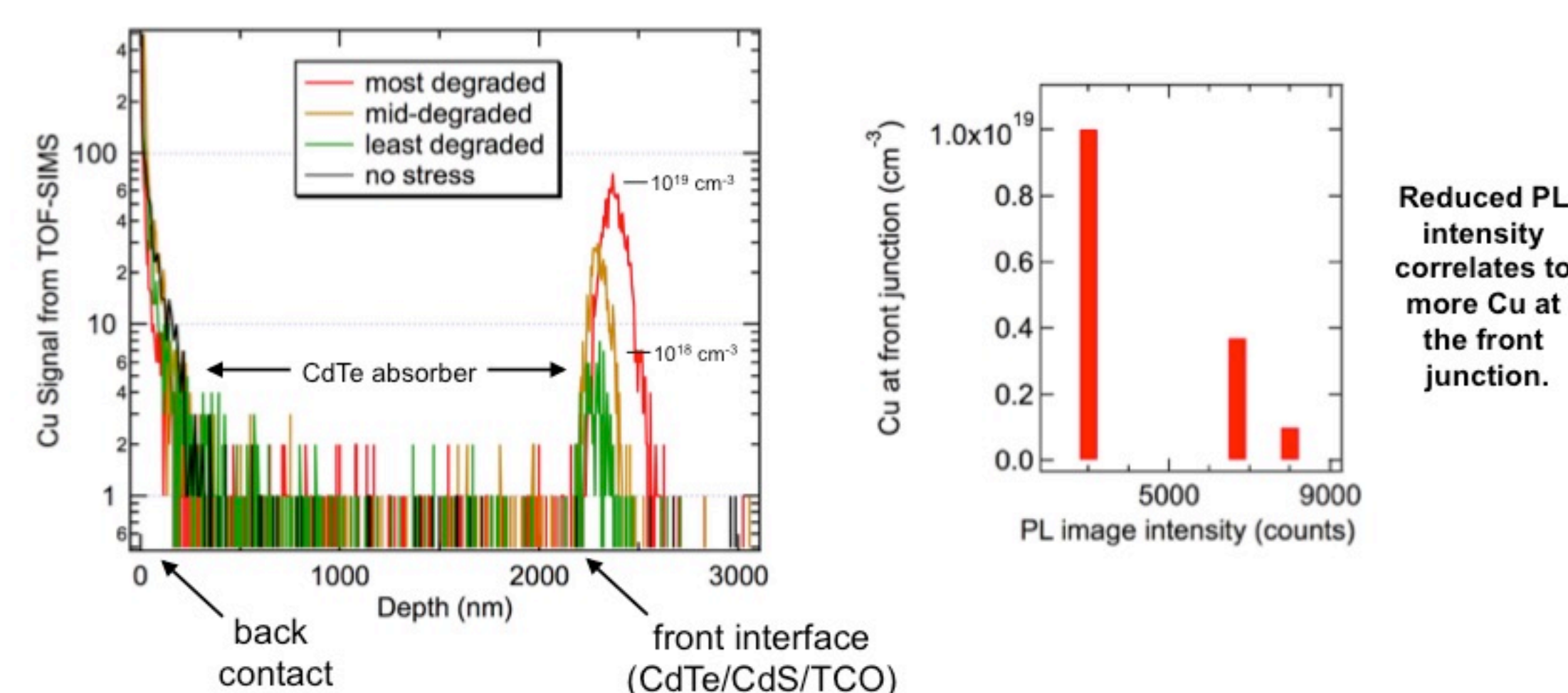


- Cut out samples from regions of interest.
- Avoid shunt areas with any grown-in defects.
- Based on PL image intensity:
 - Least degraded
 - Mid-degraded
 - Most degraded

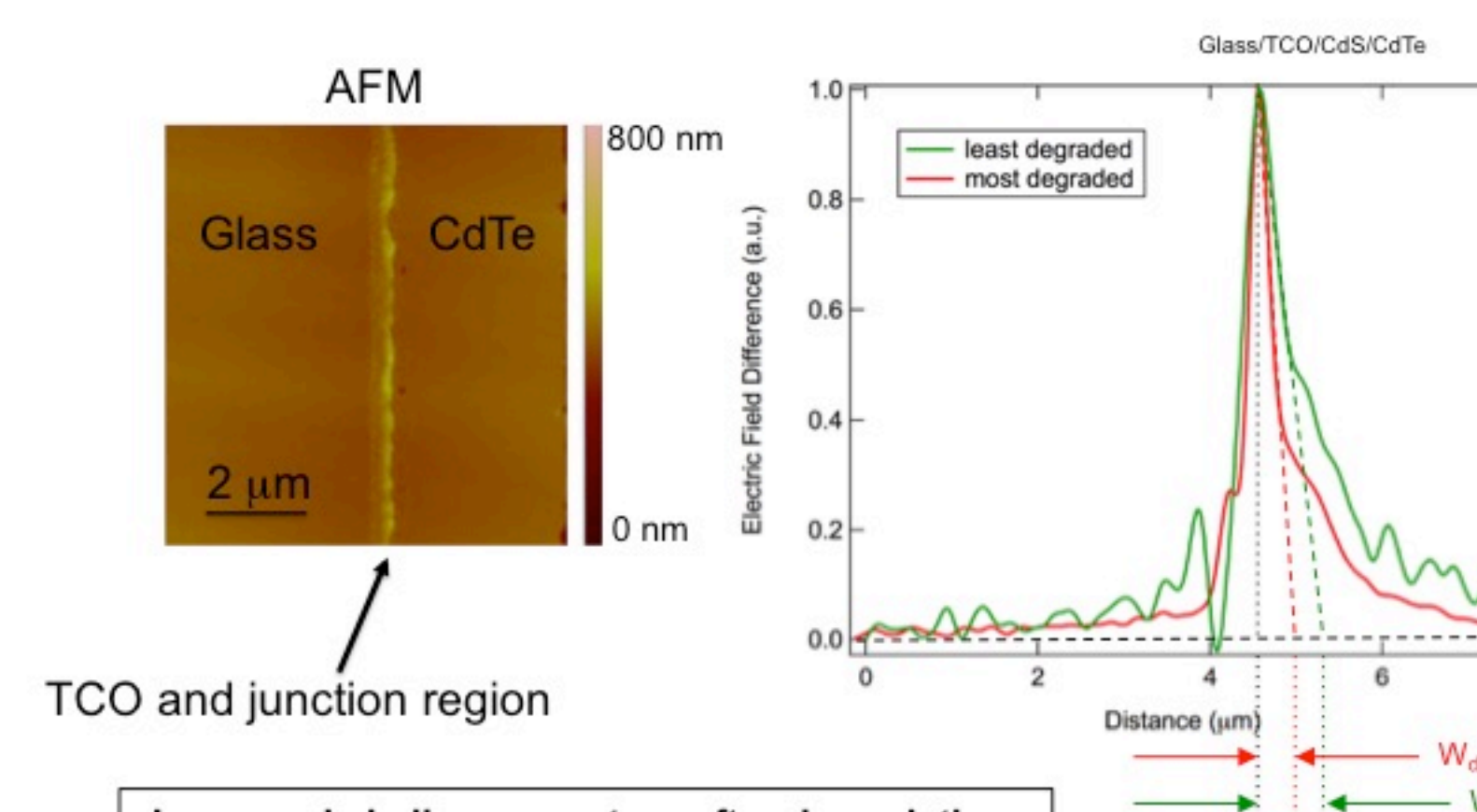
PL imaging on cored regions from degraded CdTe mini-module



Cu profiles of stressed CdTe cores using Time-of-Flight Secondary Ion Mass Spectrometry (TOF-SIMS)



Kelvin Probe Force Microscopy (KPFM) potential imaging on cross-sections of stressed CdTe cored samples

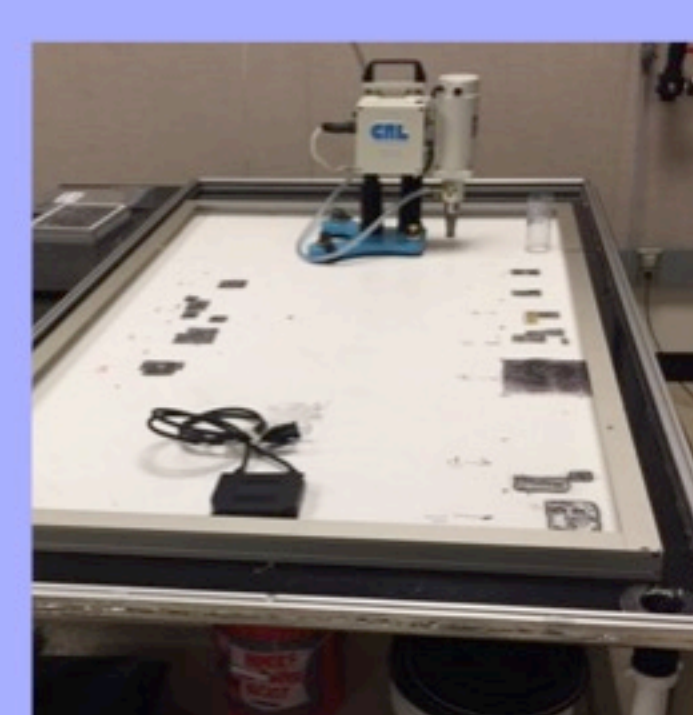


Ion transport (Cu-ions) to front junction [1] leads to both:

- shallow centers for increased doping, and
- deep defect generation
 - increased carrier recombination
 - reduced cell performance.

In [1], TRPL was inconclusive, but here, PL intensity shows correlation to degradation.

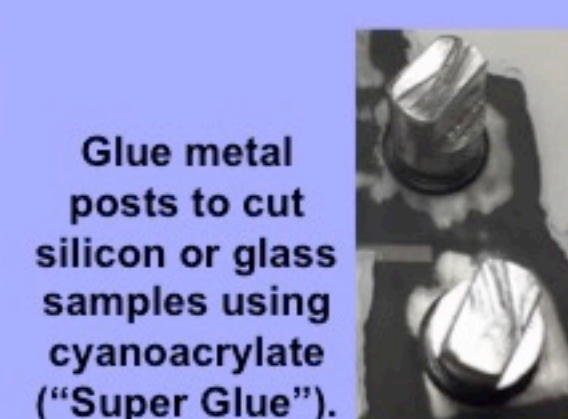
Core selected areas from degraded modules



Use diamond-based coring bit and liquid-cooled drill to cut through Si cell or thin-film and glass.



Cut sample for extraction



Glue metal posts to cut silicon or glass samples using cyanoacrylate ("Super Glue").

On thin-film modules, glue posts to cored glass, or core completely through the module and dissolve encapsulation.



Cored samples from ~12 to 25 mm diameter

After the glue is set, use a wrench to shear the sample from the module.



Soak in acetone to dissolve Super Glue and remove post. Or, use a short post that fits in measurement tools and does not need to be removed.